(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
21 March 2002 (21.03.2002)

PCT

(10) International Publication Number
WO 02/23605 A1

(51) International Patent Classification[7]: H01L 21/28

(21) International Application Number: PCT/US01/23580

(22) International Filing Date: 26 July 2001 (26.07.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/660,723 13 September 2000 (13.09.2000) US

(71) Applicant: **ADVANCED MICRO DEVICES, INC.** [US/US]; One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

(72) Inventors: **BONSER, Douglas, J.**; 5336 Magdelena Drive, Austin, TX 78735 (US). **PURDY, Matthew**; 6307 Bluff Springs Road #731, Austin, TX 78744 (US). **HUSSEY, James, H., Jr.**; 2108 Airole Way, Austin, TX 78704 (US).

(74) Agent: **DRAKE, Paul, S.**; Advanced Micro Devices, Inc., 5204 East Ben White Boulevard, Mail Stop 562, Austin, TX 78741 (US).

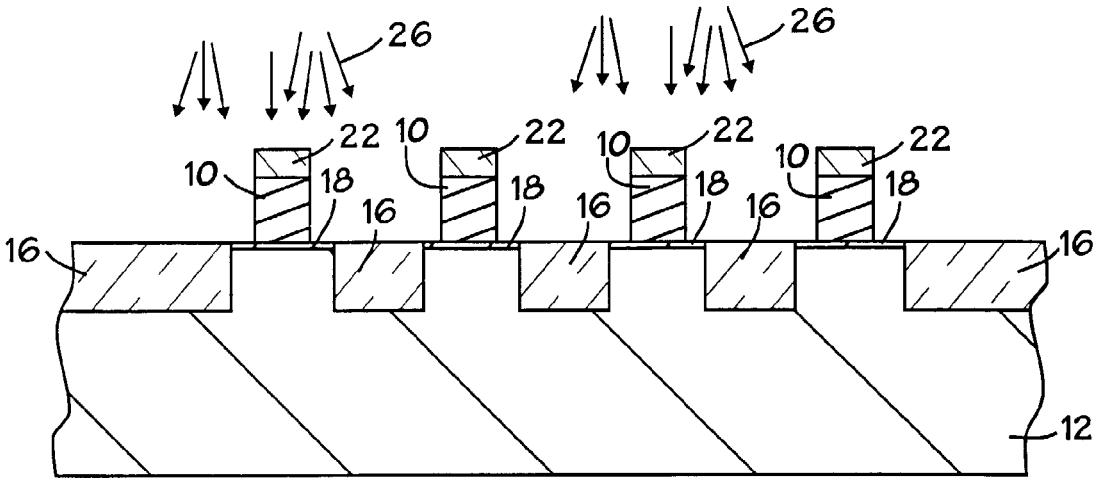
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: DRY ISOTROPIC REMOVAL OF INORGANIC ANTI-REFLECTIVE COATING AFTER POLY GATE ETCHING



(57) Abstract: Various methods of fabricating a conductor structure (10) are provided. In one aspect, a method of fabricating a conductor structure (10) on a first workpiece (12) is provided. A silicon film (20) is formed on the first workpice (12). An anti-reflective coating (22) is formed on the silicon film (20). A mask (24) is formed on a first portion of the anti-reflective coating (22), while a second portion thereof is left unmasked. The second portion of the anti-reflective coating (22) and the silicon film (20) are etched. The mask (24) is removed, and the anti-reflective coating (22) is removed by isotropic plasma etching. Use of isotropic etching for anti-reflective coating removal eliminates thermal shock associated with heated acid bath anti-reflective coating removal.

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